

Thyristor Diode Modules

AMKH 215-16E



Symbols and parameters			Values	Units
I_{TAV}	Average on-state current	sin. 180; $T_C = 85 (100)^\circ\text{C}$	215 (153)	A
I_{TSM}	Surge on-state current	$T_j = 25^\circ\text{C}; 10 \text{ ms}$	7000	A
		$T_j = 125^\circ\text{C}; 10 \text{ ms}$	5700	A
I^2t	I^2t value, rating for fusing	$T_j = 25^\circ\text{C}; 10 \text{ ms}$	245000	A^2s
		$T_j = 125^\circ\text{C}; 10 \text{ ms}$	162450	A^2s
V_{RSM}	Non-repetitive peak reverse voltage		1700	V
$V_{RRM}; V_{DRM}$	Repetitive peak reverse voltage; Repetitive peak off-state voltage		1600	V
$(di/dt)_{cr}$	Critical rate of rise of on-state current	$T_j = 125^\circ\text{C}$	200	$\text{A}/\mu\text{s}$
$(dv/dt)_{cr}$	Critical rate of rise of off-state voltage	$T_j = 125^\circ\text{C}$	1000	$\text{V}/\mu\text{s}$
T_j	Virtual junction temperature		-40 ... +125	$^\circ\text{C}$
T_{stg}	Storage temperature range		-40 ... +125	$^\circ\text{C}$
V_{ISOL}	Insulation test voltage (r.m.s.)	a.c. 50 Hz; r.m.s.; 1s / 1min.	3600 / 3000	V
V_T	On-state voltage	$T_j = 25^\circ\text{C}; I_T = 600 \text{ A}$	max. 1.5	V
$V_{T(TO)}$	On-state threshold voltage	$T_j = 125^\circ\text{C}$	max. 0.85	V
r_T	On-state slope resistance	$T_j = 125^\circ\text{C}$	max. 1.2	$\text{m}\Omega$
$I_{DD}; I_{RD}$	Forward off-state current; Direct reverse current	$T_j = 125^\circ\text{C}, V_{RD} = V_{RRM}; V_{DD} = V_{DRM}$	max. 60	mA
t_{gd}	Gate controlled turn-on delay time	$T_j = 25^\circ\text{C}; I_G = 1 \text{ A}; di_G/dt = 1 \text{ A}/\mu\text{s}$	1	μs
t_{gr}	Gate controlled rise time	$V_D = 0,67 * V_{DRM}$	2	μs
t_q	Turn-off time	$T_j = 125^\circ\text{C}$	150	μs
I_H	Holding current	$T_j = 25^\circ\text{C}; \text{typ. / max}$	150 / 400	mA
I_L	Latching current	$T_j = 25^\circ\text{C}; R_G = 33\Omega; \text{typ. / max}$	300 / 1000	mA
V_{GT}	Gate trigger voltage	$T_j = 25^\circ\text{C}; \text{d.c.}$	min. 2	V
I_{GT}	Gate trigger current	$T_j = 25^\circ\text{C}; \text{d.c.}$	min. 150	mA
V_{GD}	Gate non-trigger voltage	$T_j = 125^\circ\text{C}; \text{d.c.}$	max. 0.25	V
I_{GD}	Gate non-trigger current	$T_j = 125^\circ\text{C}; \text{d.c.}$	max. 10	mA
$R_{th(j-c)}$	Thermal resistance, junction to case	cont. DC; per chip / per module	0.12 / 0.06	K/W
		sin.180; per chip / per module	0.125 / 0.065	K/W
		rec.120; per chip / per module	0.14 / 0.07	K/W
$R_{th(c-s)}$	Thermal resistance, junction to heatsink	per chip / per module	0.04 / 0.027	K/W
M_s	Mounting torque on heatsink	min / max	4.25 / 5.75	Nm
M_t	Mounting torque for terminals	min / max	4.25 / 5.75	Nm
a	Maximum allowable acceleration		$5 * 9.81$	m/s^2
W	Weight	approx.	165	g

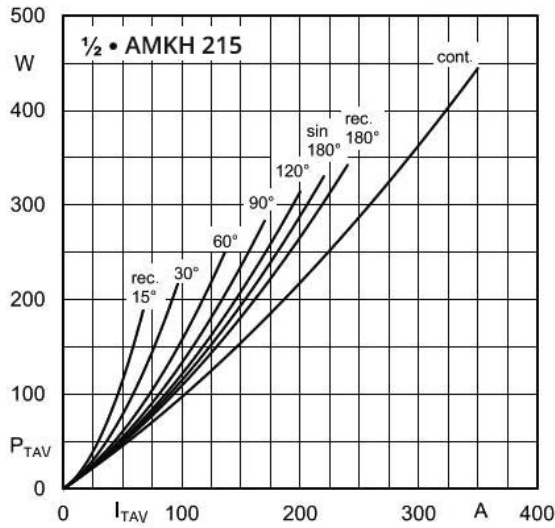


Fig. 1L: Power dissipation per thyristor vs. on-state current

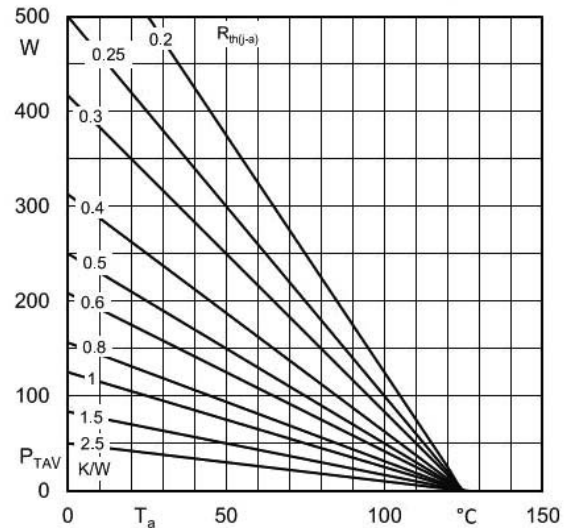


Fig. 1R: Max. power dissipation per chip vs. ambient temperature

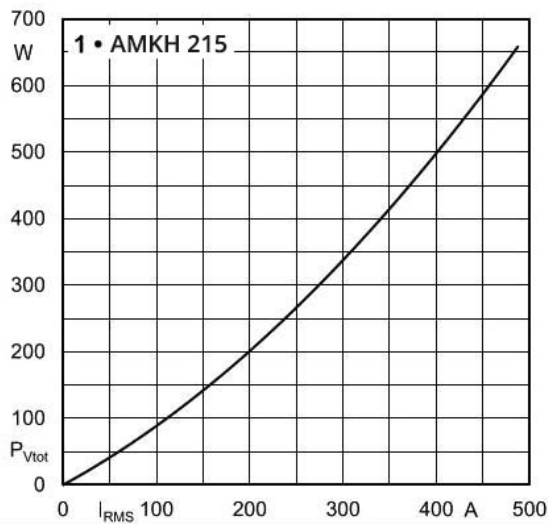


Fig. 2L: Max. power dissipation of one module vs. rms current

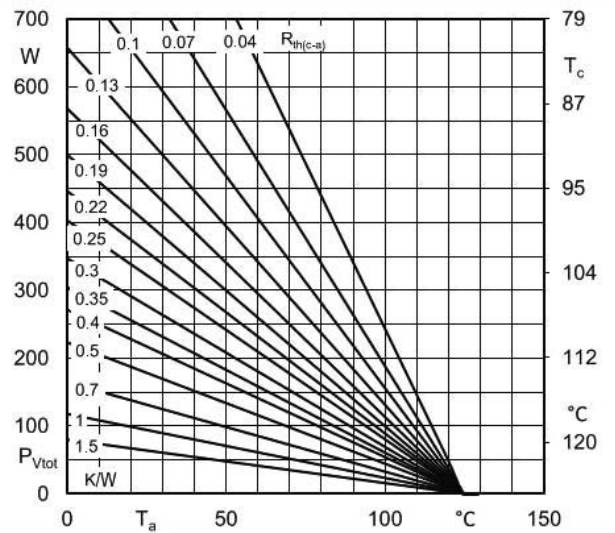


Fig. 2R: Max. power dissipation of one module vs. case temperature

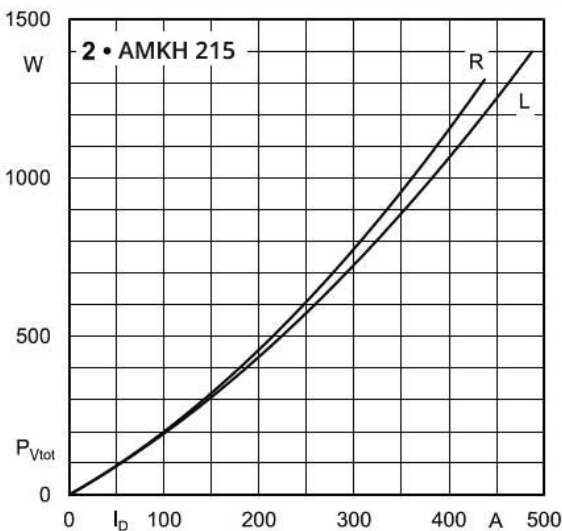


Fig. 3L: Max. power dissipation of two modules vs. direct current

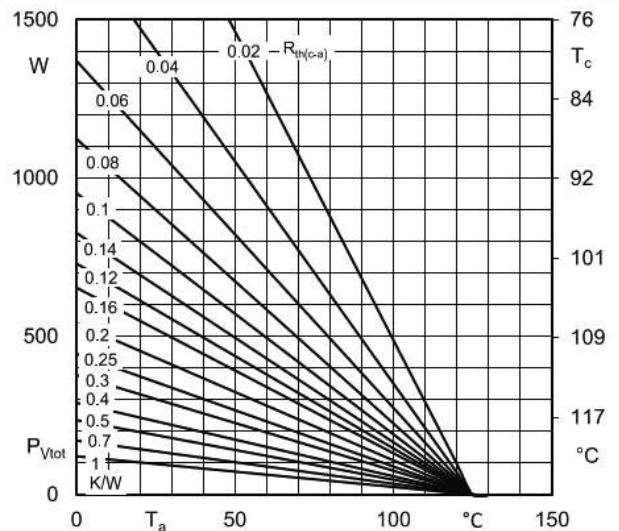


Fig. 3R: Max. power dissipation of two modules vs. case temperature

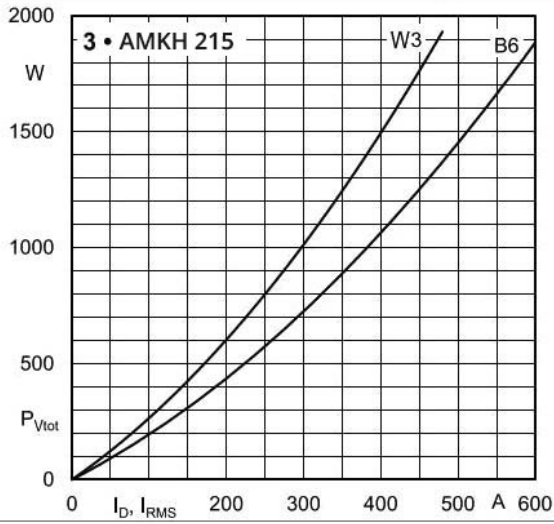


Fig. 4L: Max. power dissipation of three modules vs. direct current

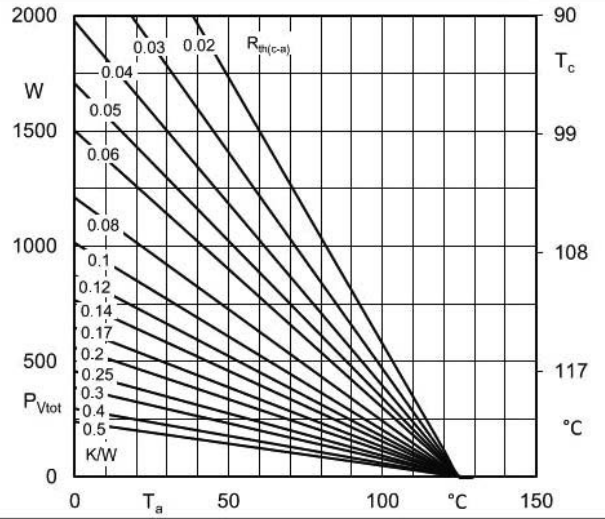


Fig. 4R: Max. power dissipation of three modules vs. case temperature

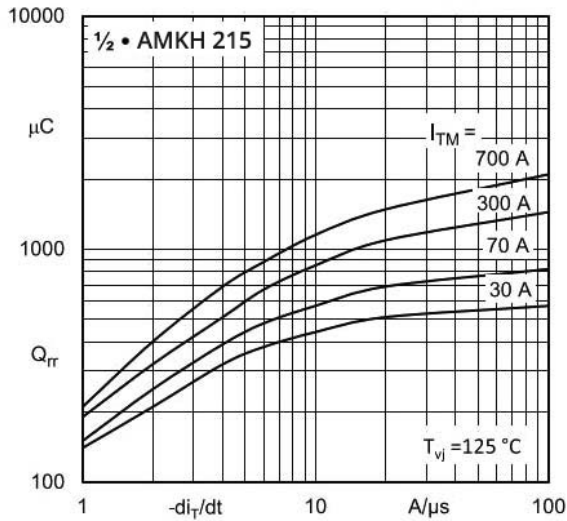


Fig. 5: Recovered charge vs. current decrease

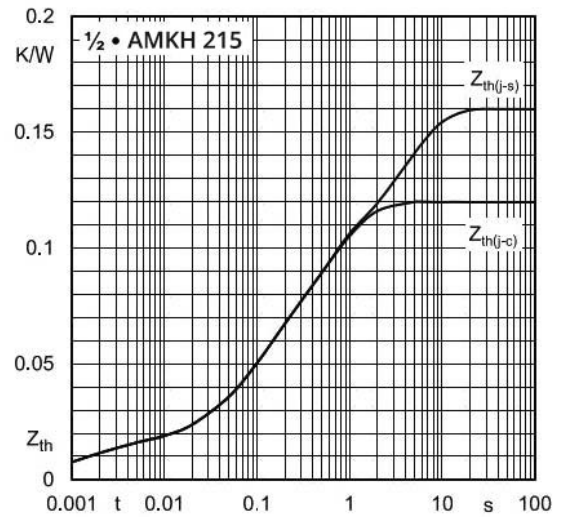


Fig. 6: Transient thermal impedance vs. time

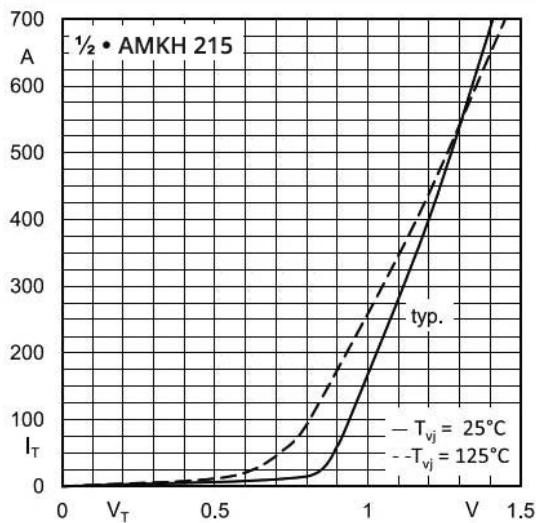


Fig. 7: On-state characteristics

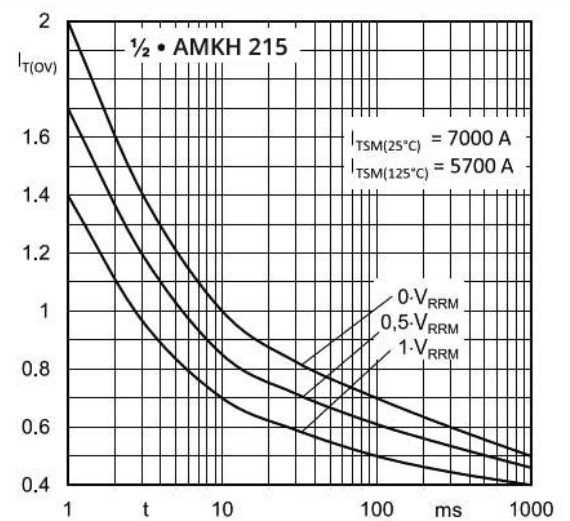


Fig. 8: Surge overload current vs. time

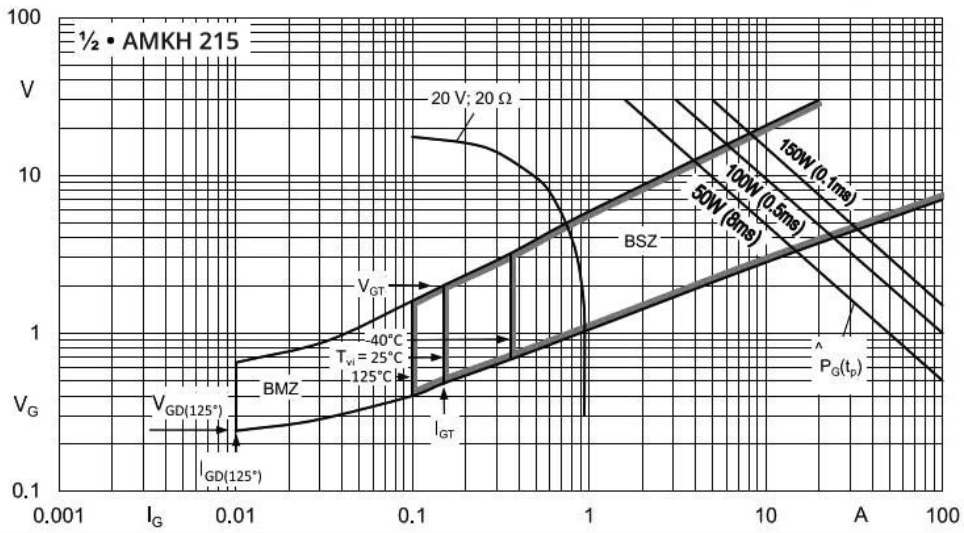
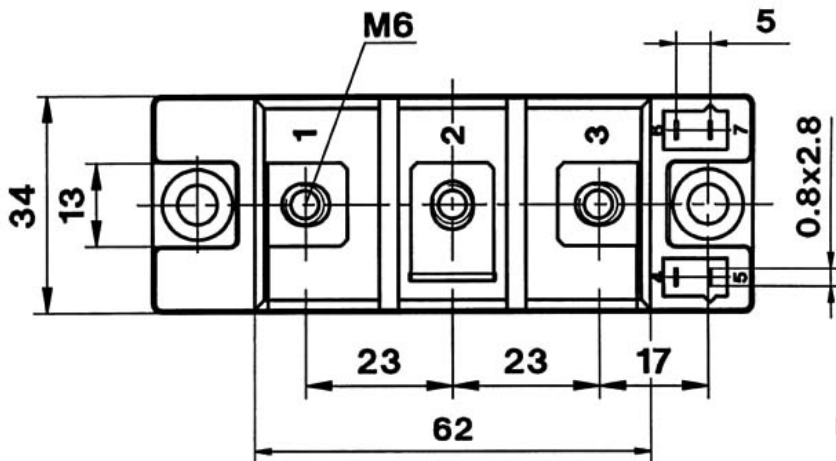
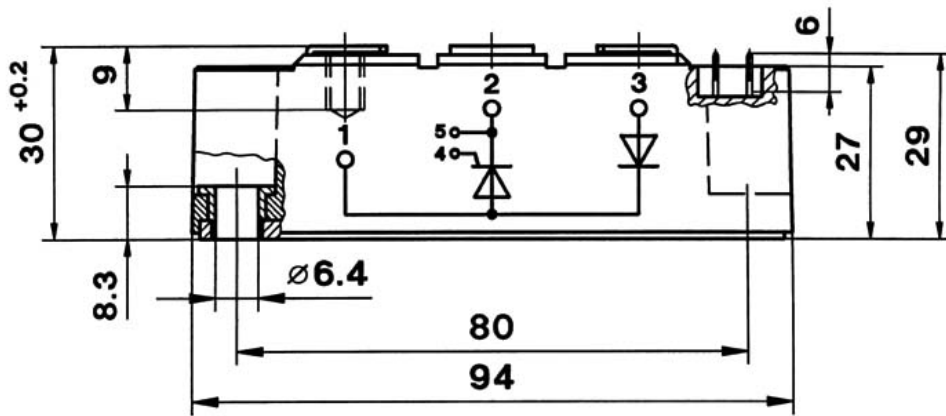


Fig. 9: Gate trigger characteristics

DIMENSIONS



Dimensions in mm

TOPOLOGY OF INTERNAL CONNECTION

